N-Ch and P-Ch Fast Switching MOSFETs

★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

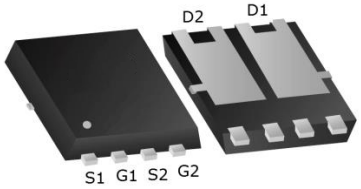
BVDSS	RDSON	ID
40V	17mΩ	10A
-40V	39mΩ	-10A

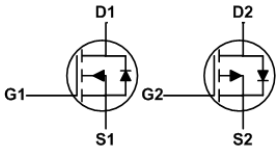
Description

The XXW40G10D is the high performance complementary N-ch and P-ch MOSFETs with high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The XXW40G10D meet the RoHS and Green

PDFN3333-8L Pin Configuration





Absolute Maximum Ratings (T_A=25℃ unless otherwise specified)

Symbol	Parameter		Max. N-Channel	Max. P-Channel	Units
V_{DSS}	Drain-Source Voltage		40	-40	V
V_{GSS}	Gate-Source Voltage		±20	±20	V
I_D	Continuous Drain Current	T_A = 25℃	10	-10	A
		T_A = 100℃	5.2	-3.9	A
I_{DM}	Pulsed Drain Current note1		32	-24	A
E_{AS}	Single Pulsed Avalanche Energy note2		13	17.6	mJ
P_D	Power Dissipation	T_A = 25℃	2	3.2	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		62.5	39	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		℃

N-Channel Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=40V, V_{GS}=0V	-	-	1.0	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	1.0	1.5	2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}=10V, I_D=8A	-	17	22	mΩ
		V_{GS}=4.5V, I_D=5A	-	25	35	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=20V, V_{GS}=0V, f=1.0MHz	-	633	-	pF
C_{oss}	Output Capacitance		-	67	-	pF
C_{rss}	Reverse Transfer Capacitance		-	58	-	pF
Q_g	Total Gate Charge	V_{DS}=20V, I_D=8A, V_{GS}=10V	-	12	-	nC
Q_{gs}	Gate-Source Charge		-	3.2	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= 20V, R_L =2.5Ω V_{GS}=10V,R_{REN} =3Ω	-	4	-	ns
t_r	Turn-on Rise Time		-	3	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	15	-	ns
t_f	Turn-off Fall Time		-	2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	10	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= 8A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition : T_J=25℃,V_{DD}=20V,V_G=10V,L=0.5mH,Rg=25Ω,I_{AS}=7.2A

T_J=25℃,V_{DD}=-20V,V_G= -10V,L=0.5mH,Rg=25Ω,I_{AS}=-8.4A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

P-Channel Electrical Characteristics (T_J=25℃ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D= -250μA	-40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -40V, V_{GS}=0V	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	V_{DS}=0V, V_{GS}=±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D= -250μA	-1.0	-1.6	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance note3	V_{GS}= -10V, I_D= -6A	-	39	53	mΩ
		V_{GS}= -4.5V, I_D= -4A	-	58	81	
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}= -20V, V_{GS}=0V, f=1.0MHz	-	860	-	pF
C_{oss}	Output Capacitance		-	87	-	pF
C_{rss}	Reverse Transfer Capacitance		-	70	-	pF
Q_g	Total Gate Charge	V_{DS}= -20V, I_D= -6A, V_{GS}= -10V	-	13	-	nC
Q_{gs}	Gate-Source Charge		-	3.8	-	nC
Q_{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}= -20V, R_L =2.3Ω V_{GS}=-10V,R_{REN} =6Ω	-	7.5	-	ns
t_r	Turn-on Rise Time		-	5.5	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	19	-	ns
t_f	Turn-off Fall Time		-	7	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-24	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS}=0V, I_S= -6A	-	-	-1.2	V

Typical Performance Characteristics-N

Figure1: Output Characteristics

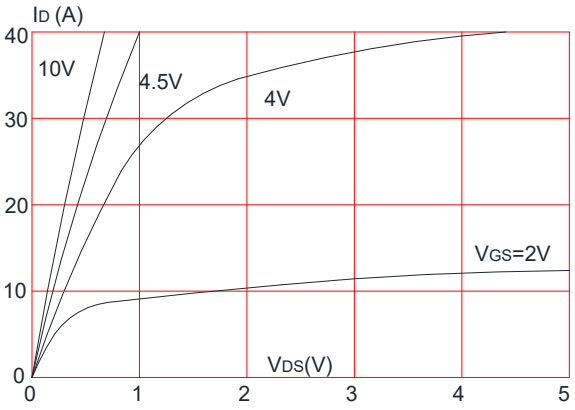


Figure 2: Typical Transfer Characteristics

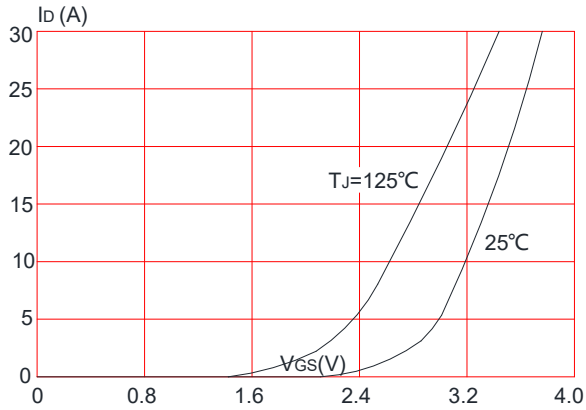


Figure 3: On-resistance vs. Drain Current

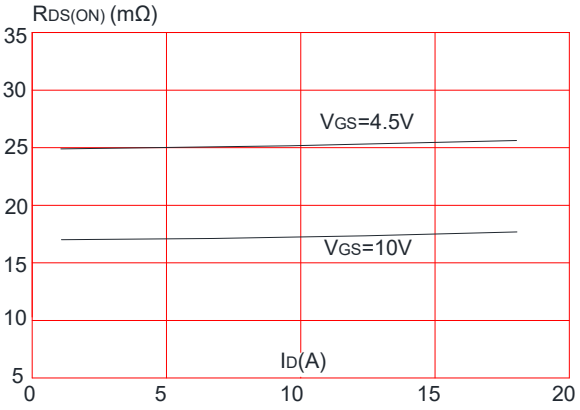


Figure 4: Body Diode Characteristics

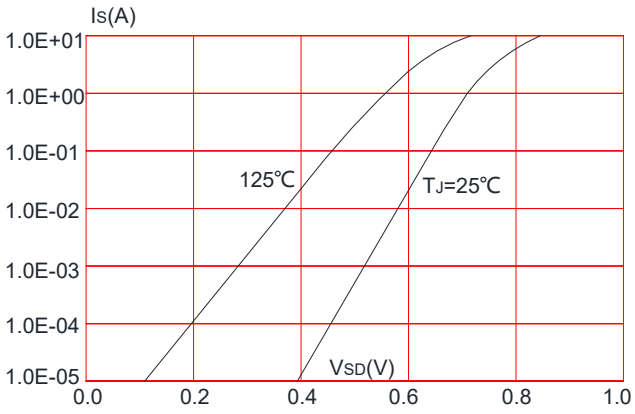


Figure 5: Gate Charge Characteristics

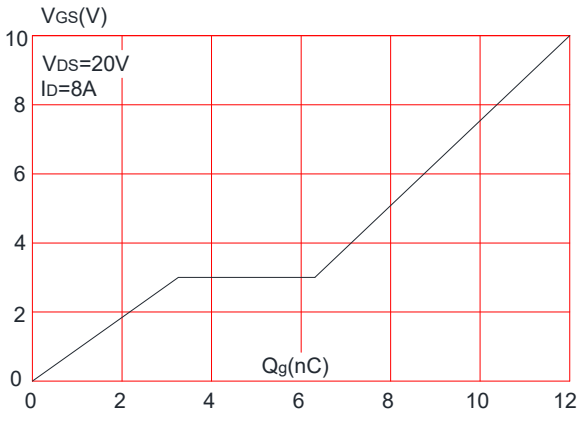


Figure 6: Capacitance Characteristics

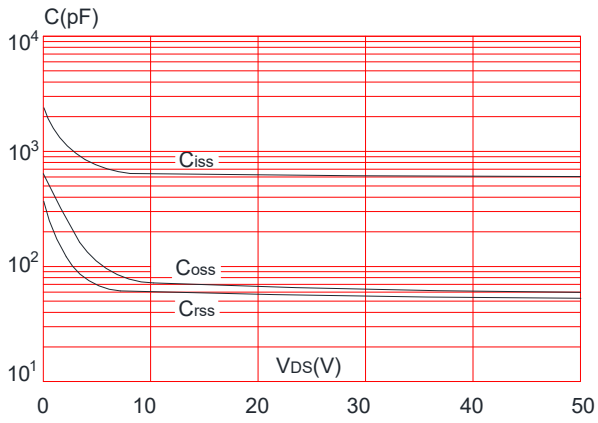


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

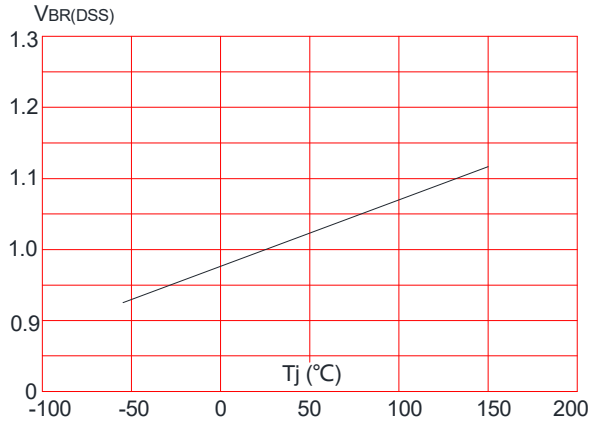


Figure 8: Normalized on Resistance vs. Junction Temperature

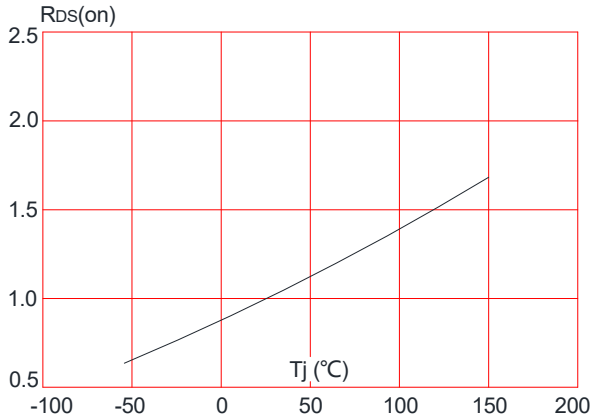


Figure 9: Maximum Safe Operating Area

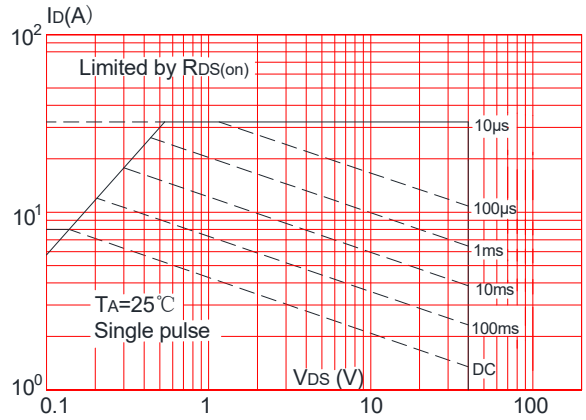


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

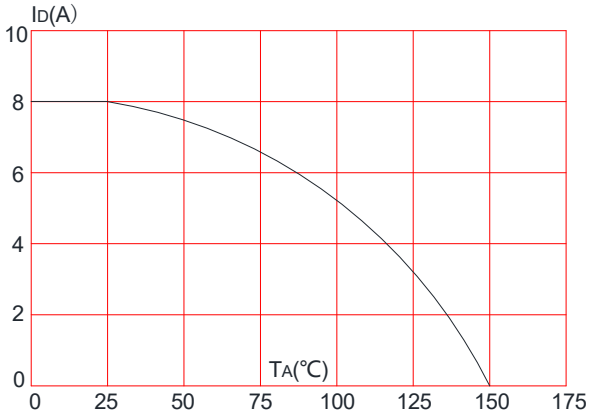
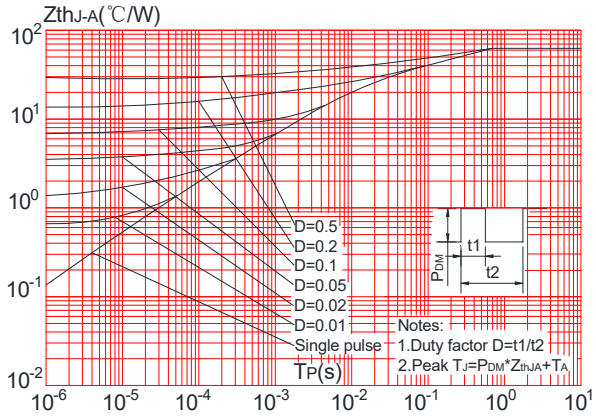


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Typical Performance Characteristics-P

Figure1: Output Characteristics

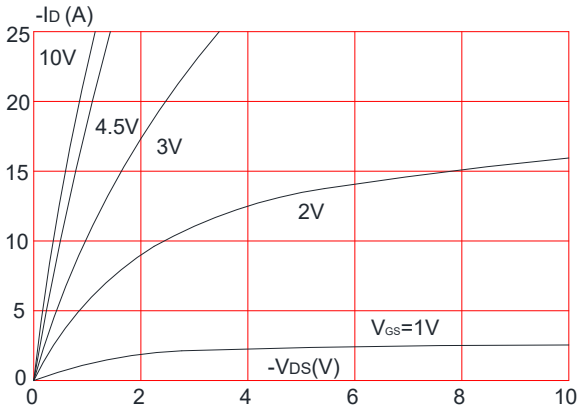


Figure 2: Typical Transfer Characteristics

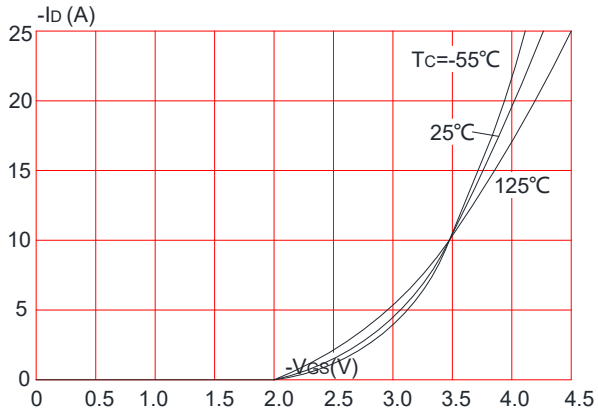


Figure 3: On-resistance vs. Drain Current

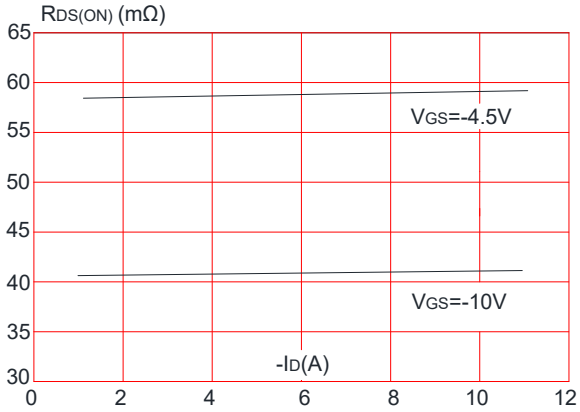


Figure 4: Body Diode Characteristics

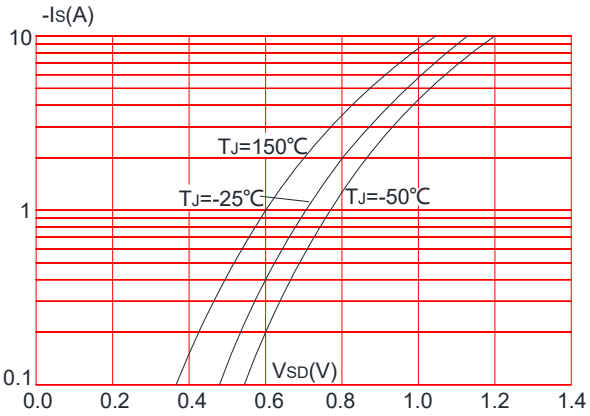


Figure 5: Gate Charge Characteristics

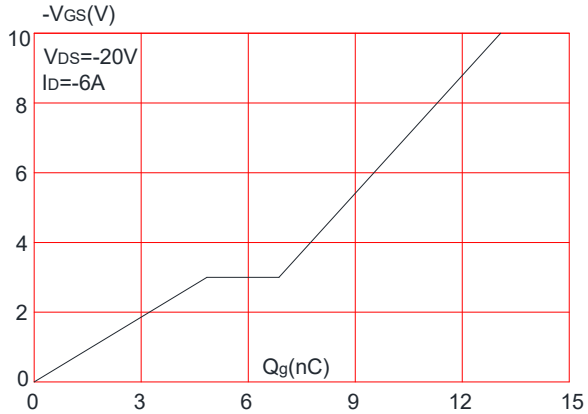


Figure 6: Capacitance Characteristics

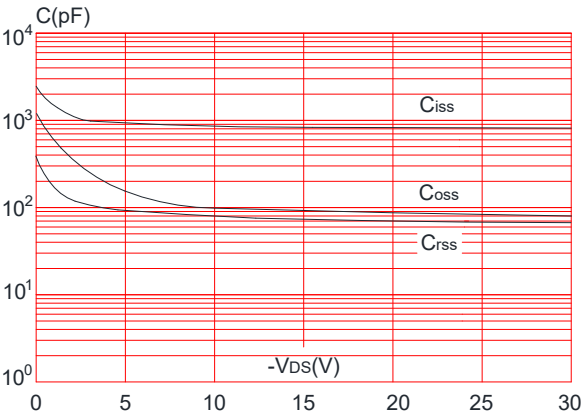


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

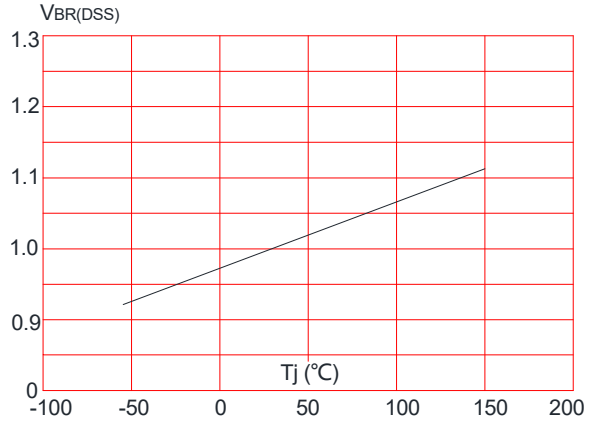


Figure 8: Normalized on Resistance vs. Junction Temperature

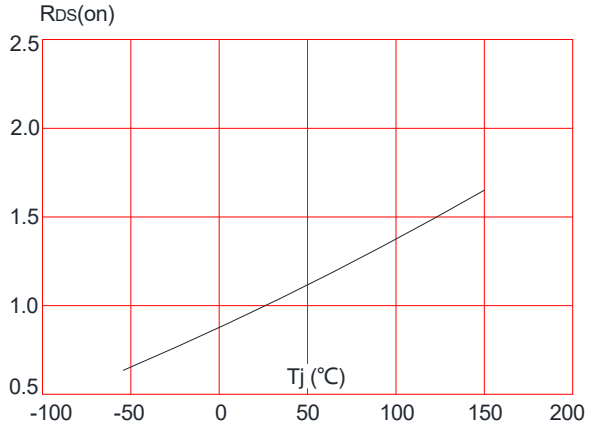


Figure 9: Maximum Safe Operating Area

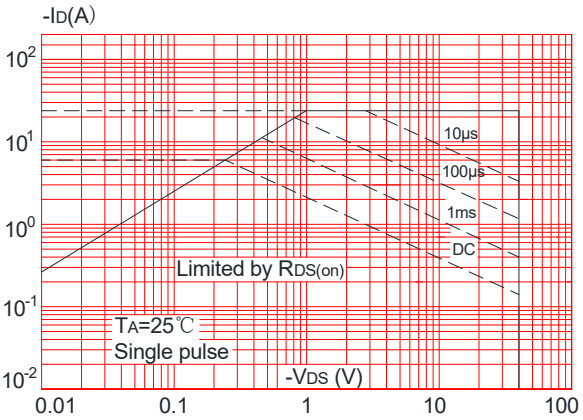


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

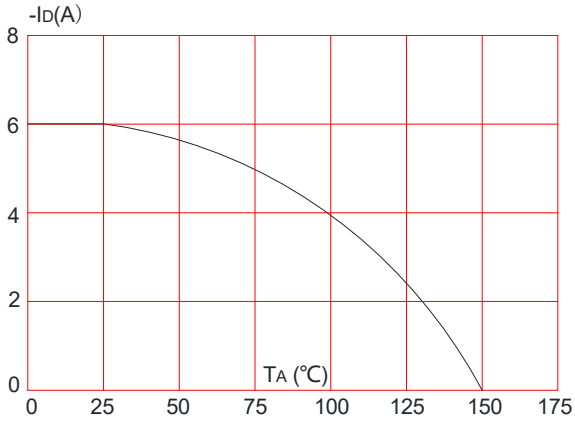
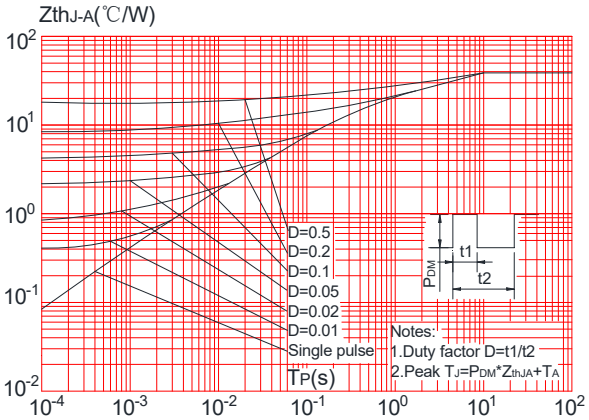
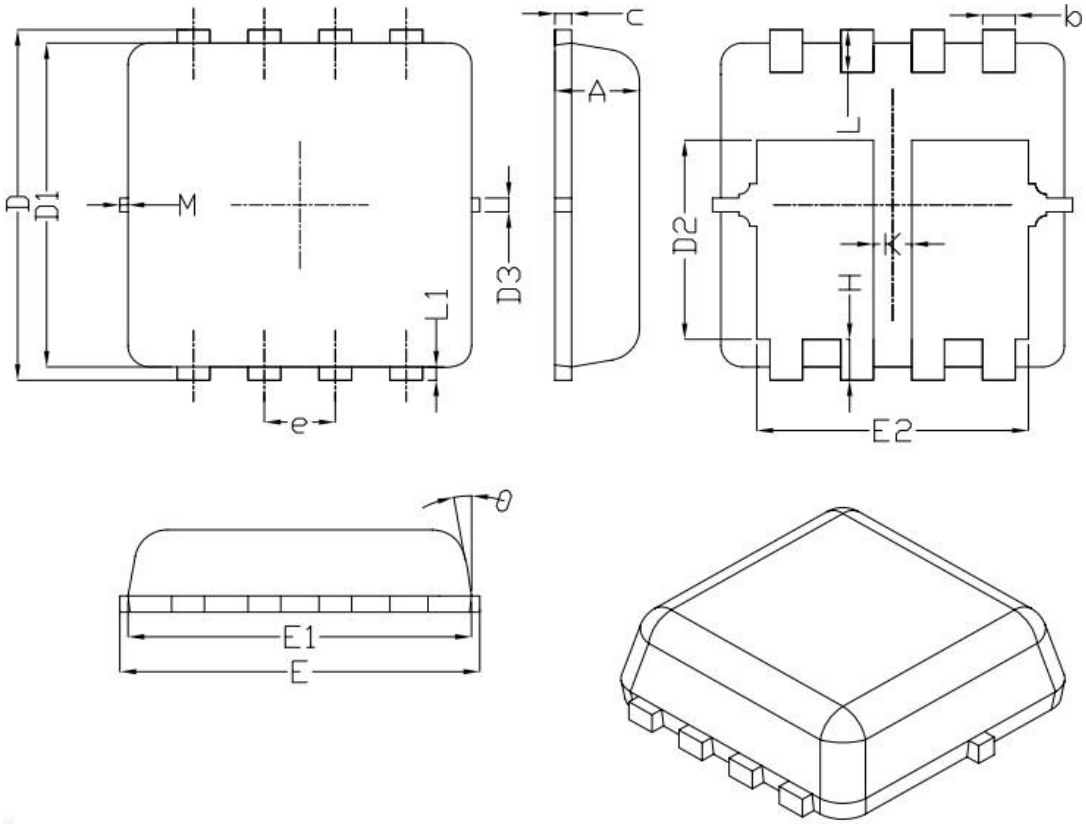


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



Dual PDFN3333-8L Package Outline Data



Symbol	Dimensions (unit: mm)		
	Min	Typ	Max
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.78	1.88	1.98
D3	--	0.13	--
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65 BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	--	0.13	--
K	0.30	--	--
θ	--	10°	12°
M	*	*	0.15
* Not Specified			

Notes:

1. Refer to JEDEC MO-240 variation CA.
2. Dimensions "D1" and "E1" do NOT include mold flash protrusions or gate burrs.
3. Dimensions "D1" and "E1" include interterminal flash or protrusion.